

AUFB8409-VB Datasheet

N-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00084
I _D (A)	409
Configuration	Single
Qg (nC)	250

FEATURES

- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

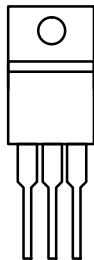
APPLICATIONS

- Synchronous Rectification
- Power Supplies

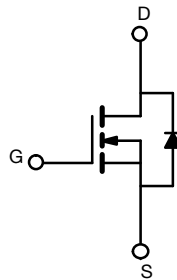


RoHS
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HALOGEN
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TO-220AB



G D S
Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	40	V
Gate-source voltage		V _{GS}	± 20	
Continuous drain current ^a	T _C = 25 °C	I _D	409	A
	T _C = 125 °C		320	
Continuous source current (diode conduction) ^a		I _S	409	
Pulsed drain current ^b		I _{DM}	600	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	100	
Single pulse avalanche energy		E _{AS}	500	
Maximum power dissipation ^b	T _C = 25 °C	P _D	375	W
	T _C = 125 °C		125	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	40	°C/W
Junction-to-case (drain)		R _{thJC}	0.4	

Notes

- Based on T_C = 25 °C.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)

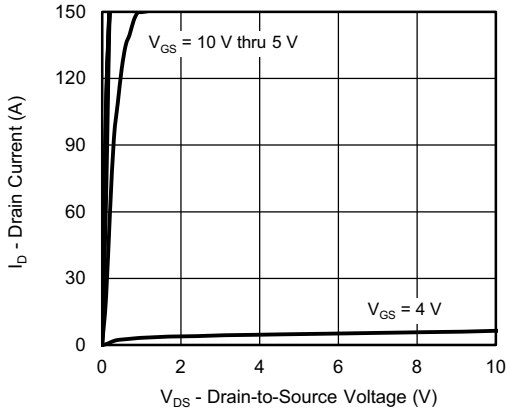
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.5	3.0	3.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	300	μA
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	100	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 35 A	-	0.00084	-	Ω
		V _{GS} = 10 V	I _D = 35 A, T _J = 125 °C	-	0.00140	-	
		V _{GS} = 10 V	I _D = 35 A, T _J = 175 °C	-	0.00164	-	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 30 A		-	196	-	S
Dynamic^b							
Input capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	11 938	15 525	pF
Output capacitance	C _{oss}			-	11 163	14 520	
Reverse transfer capacitance	C _{rss}			-	282	370	
Total gate charge ^c	Q _g	V _{GS} = 10 V	V _{DS} = 20 V, I _D = 100 A	-	158	250	nC
Gate-source charge ^c	Q _{gs}			-	44	-	
Gate-drain charge ^c	Q _{gd}			-	22	-	
Gate resistance	R _g	f = 1 MHz		2.70	5.44	8.20	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 0.2 Ω I _D ≅ 100 A, V _{GEN} = 10 V, R _g = 1 Ω		-	16	25	ns
Rise time ^c	t _r			-	10	17	
Turn-off delay time ^c	t _{d(off)}			-	103	160	
Fall time ^c	t _f			-	61	95	
Source-Drain Diode Ratings and Characteristics^b							
Pulsed current ^a	I _{SM}			-	-	260	A
Forward voltage	V _{SD}	I _F = 60 A, V _{GS} = 0 V		-	0.81	1.5	V
Body diode reverse recovery time	t _{rr}	I _F = 30 A, di/dt = 100 A/μs		-	165	350	ns
Body diode reverse recovery charge	Q _{rr}			-	530	1100	nC
Reverse recovery fall time	t _a			-	66	-	ns
Reverse recovery rise time	t _b			-	99	-	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-6.2	-	A

Notes

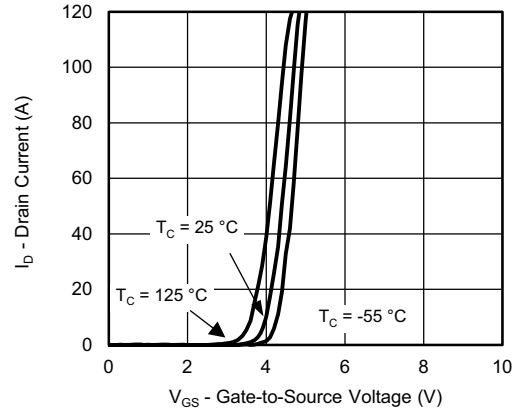
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

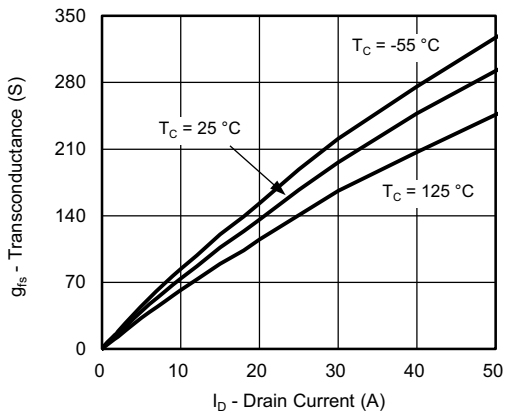
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



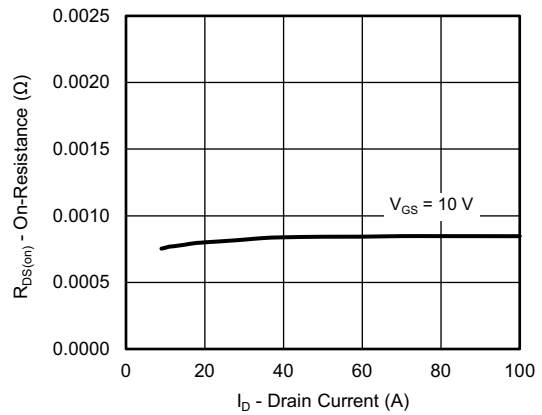
Output Characteristics



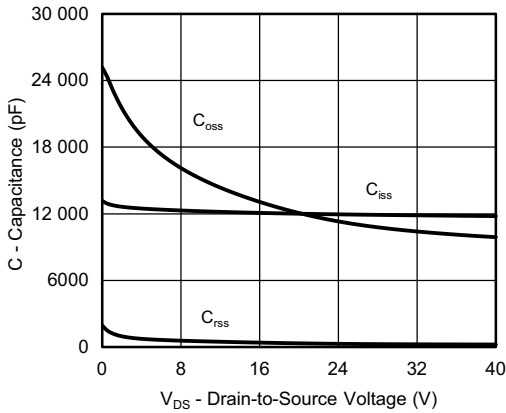
Transfer Characteristics



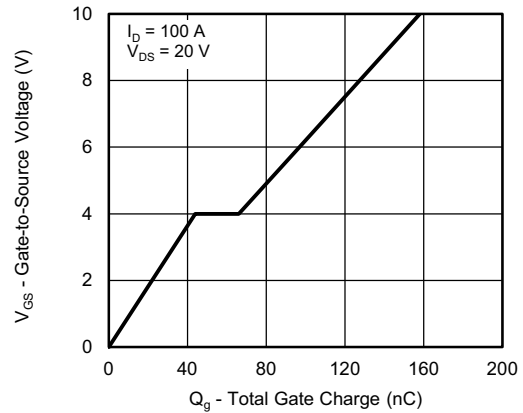
Transconductance



On-Resistance vs. Drain Current

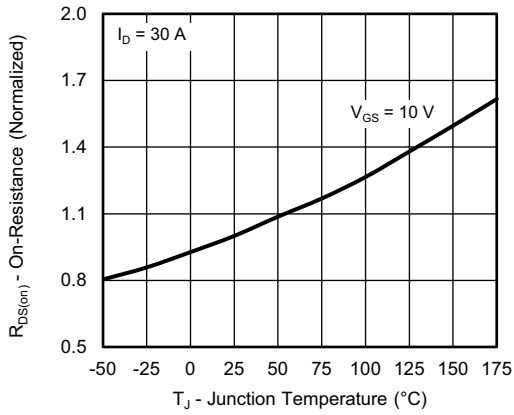


Capacitance

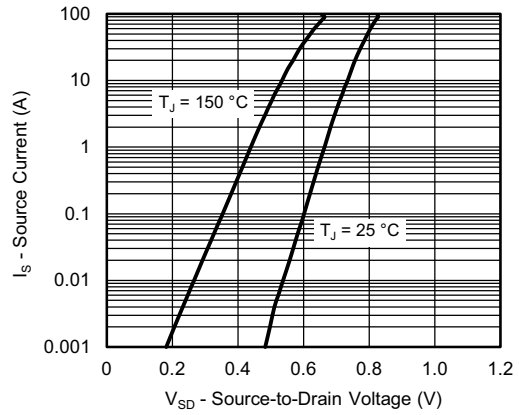


Gate Charge

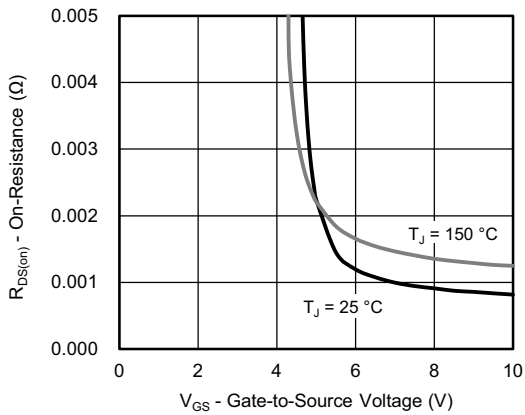
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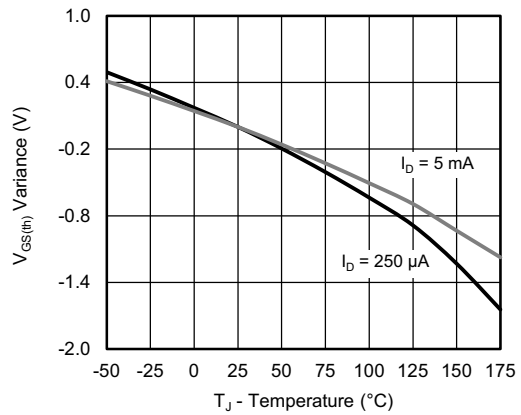
On-Resistance vs. Junction Temperature



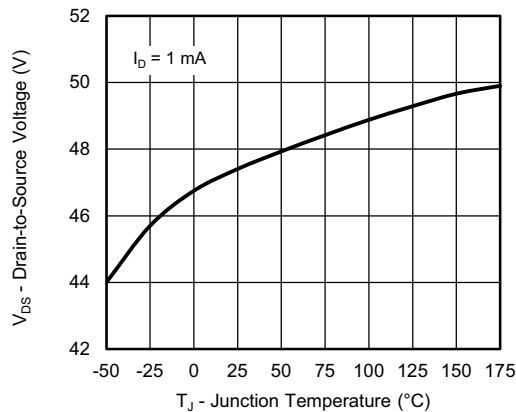
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

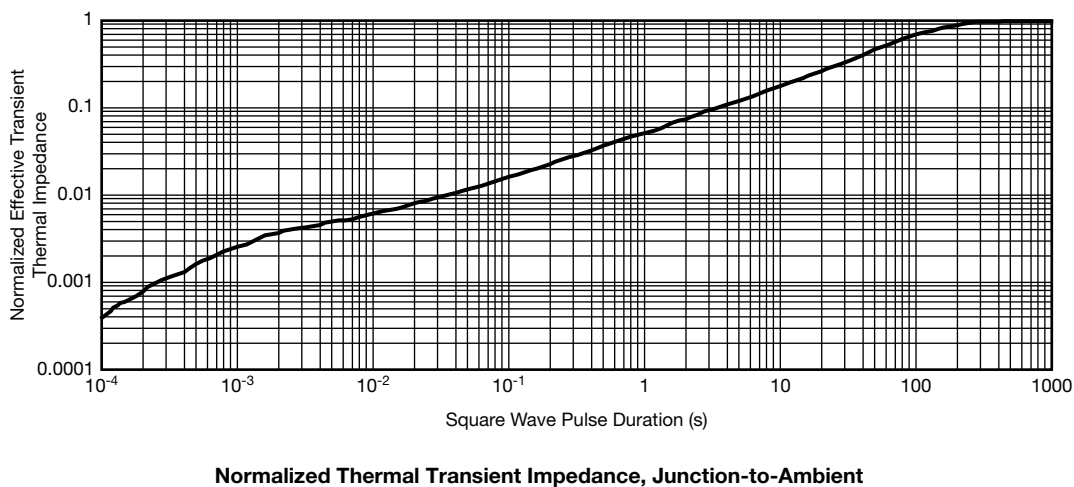
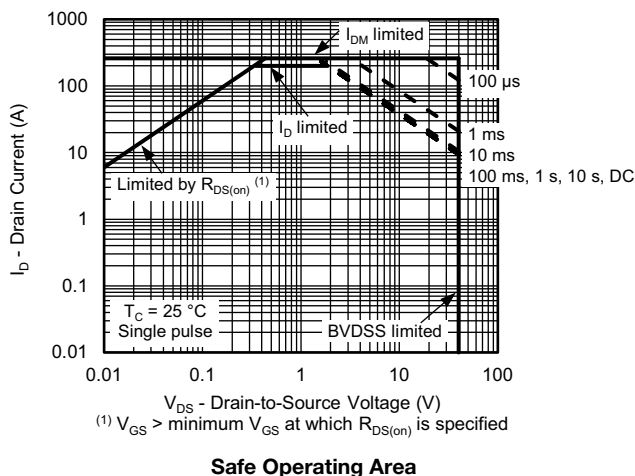


Threshold Voltage

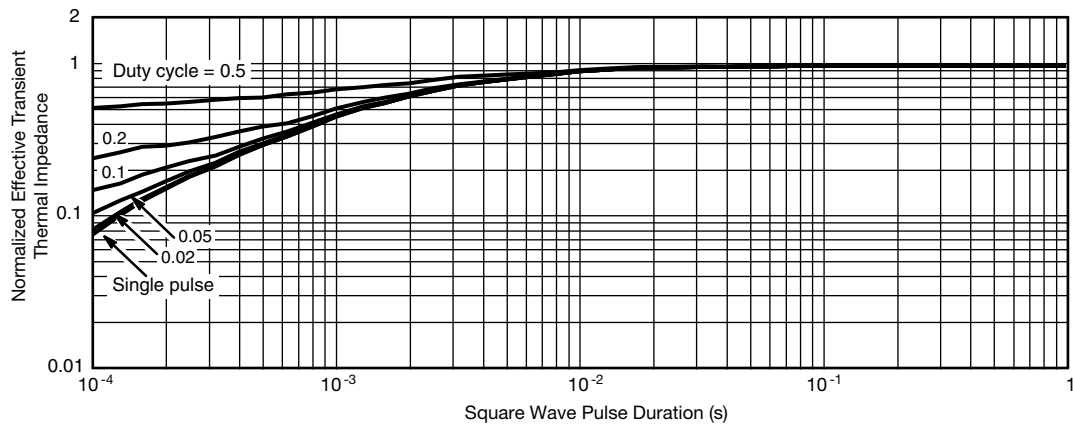


Drain Source Breakdown vs. Junction Temperature

THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

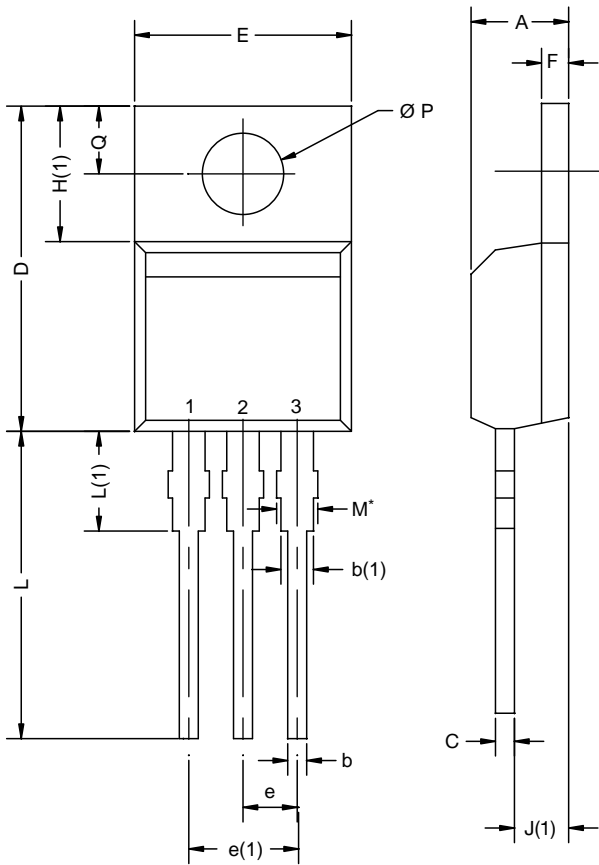


Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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